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Atomistic simulations of plasma-wall interactions on the materials side: methods and some recent results

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Greets from the capital of a snowy Finland



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Fusion reactor mat's

M Sc Jussi Polvi Processing of cellulose



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M Sc Andrey Ilinov Nanomechanics



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M Sc Laura Bukonte Fusion reactor mat/ls



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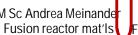
Nanostructures



Mr Fredric Granberg* Nanowires









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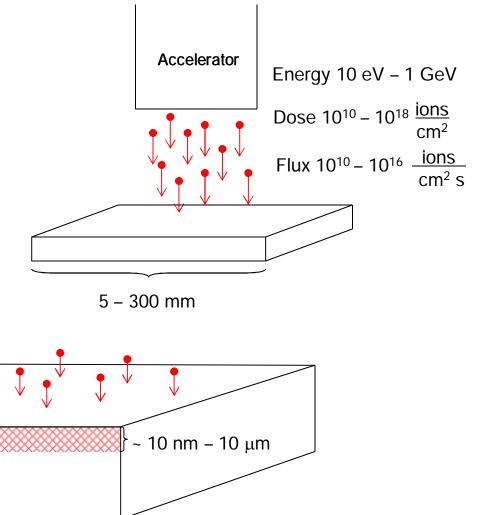
- Irradiation effects in materials
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 - Relation to ion irradiation
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 - The conventional methods:
 - Binary collision approximation (BCA)
 - Molecular dynamics (MD)
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 - Features specific to ion irradiation and plasma-wall interactions
- Some results on plasma-wall interactions
 - Swift chemical sputtering of carbon
 - Hydrogen in W by DFT, MD, KMC, rate equations

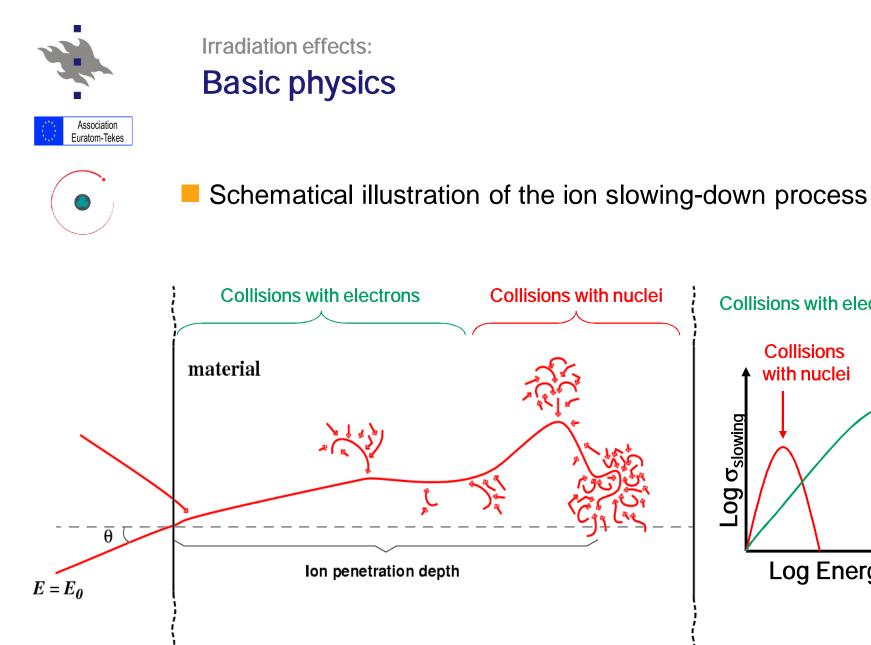


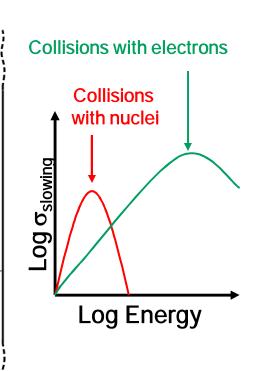
Irradiation effects in materials
Background



- Materials modification with ion beams: ions from an accelerator are shot into a material
- Huge (~ G€) business in semiconductor industry!
- Extensively studied since 1950's or so.

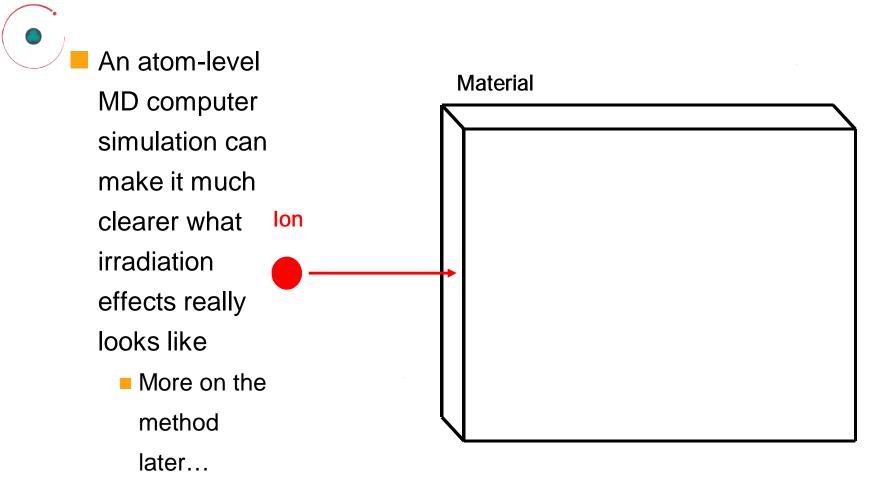








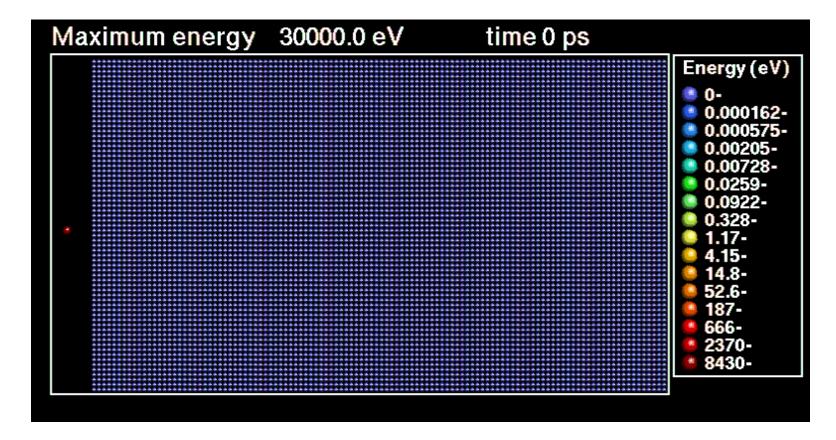
Plasma-wall interactions: Animation view





Animation view





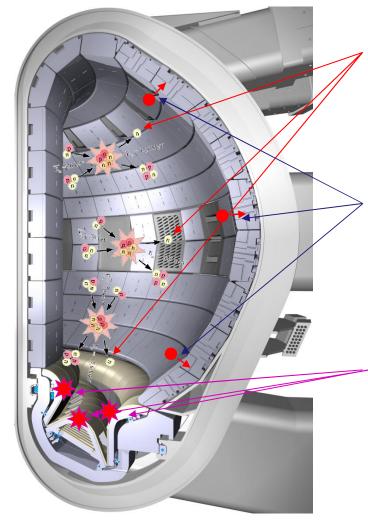


Association Euratom-Tekes





Plasma-wall interactions in fusion reactors – they are ion irradiation



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D+T fusion reaction in ITER and future fusion power plants will produce lots of 14.4 MeV neutrons and 3.5 MeV alphas

The alphas & other ions & neutrals leaking from the plasma bombard the main wall

- He energy ~ 1 MeV
- Others ~ 10 keV 1 MeV
- Flux high

Divertor is bombarded by D, T and He leaking from the plasma

- Energies ~ 1 eV 1 KeV
- Flux very high, ~ 10²⁰ ions/cm²s

[Thanks to Dr. Taina Kurki-Suonio for useful discussions on this issue]



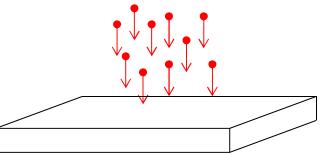
Plasma-wall energies and fluxes

- How do ions hit a material?
- From an accelerator, with a well-defined single energy E₀ with very little energy spread
 - **Time between impacts** $\sim \mu s s$

on a nanometer scale =>

each impact independent

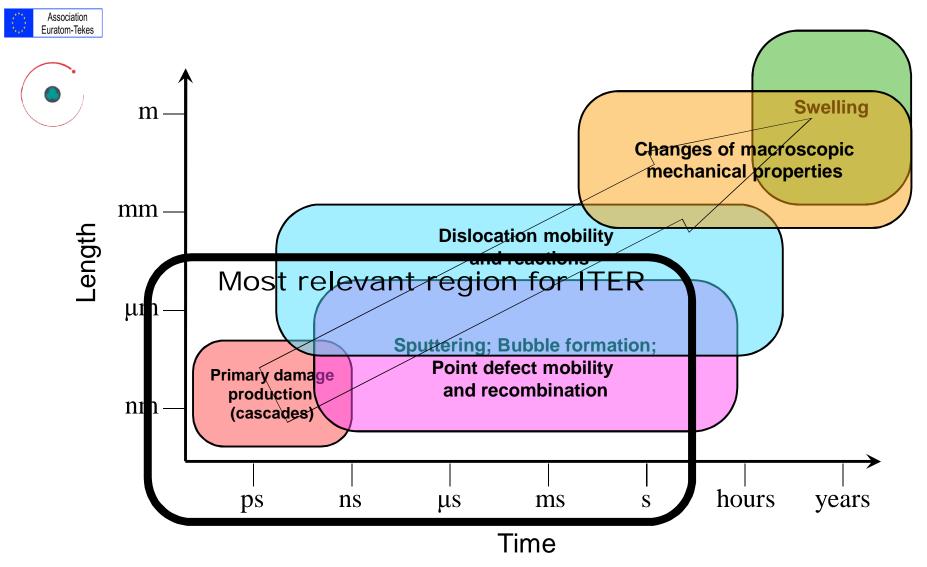
of each other



 But from a plasma more complex: energy distribution likely has Maxwell-Boltzmann distribution + ions are accelerated over sheath potential before hitting materials
 If fluxes large, impacts can be close to each other in time
 In an arc plasma, they can actually be overlapping in time!



What happens physically in the materials?

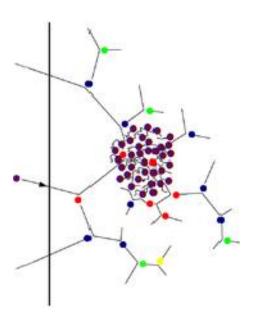


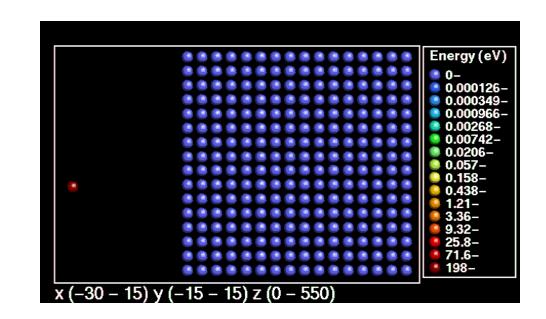




The rich materials science of plasma-wall interactions

- This is a demanding (and hence fun! ②) range of materials physics issues to work on.
- First stage: collision cascade by single incoming ion
 Simplified view:





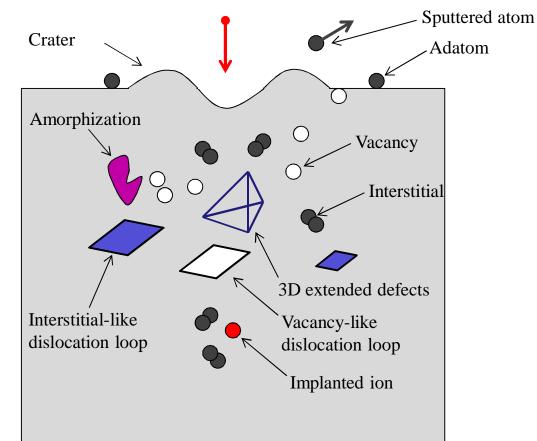
[Wikipedia by Kai Nordlund]



The rich materials science of plasma-wall interactions

But actually much more is going on.

Just for a single ion all of the below may be produced:





The rich materials science of plasma-wall interactions: high fluences



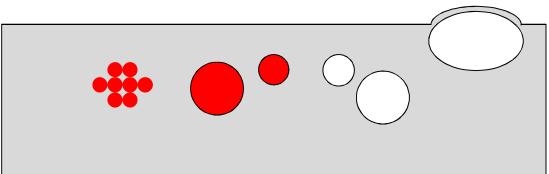
Association

- In addition, for multiple ions i.e. prolonged irradiation many more things can happen, for instance:
 - Spontaneous roughening/ripple formation



[T. K. Chini, F. Okuyama, M. Tanemura, and **K. Nordlund,** Phys. Rev. B **67**, 205403 (2003); Norris et al, Nature communications **2**, 276 (2011)]

Precipitate/nanocluster, bubble, void or blister formation inside solid

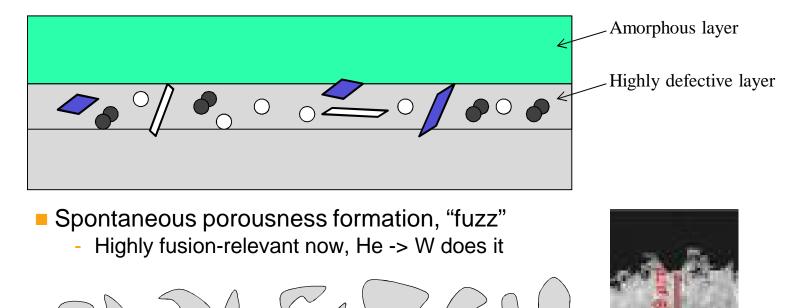


[Bubbles e.g: K. O. E. Henriksson, **K. Nordlund**, J. Keinonen, D, Physica Scripta **T108**, 95 (2004); Nanocrystals e.g. 75S. Dhara, Crit. Rev. Solid State Mater. Sci. 32, 1 [2007)]



The rich materials science of plasma-wall interactions: high fluences

Phase changes, e.g. amorphization:



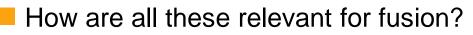
[http://vlt.ornl.gov/research/201 10119_highlight_doerner.pdf]

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Association Euratom-Tekes **Plasma-wall interactions:**

Consequences of plasma-wall interactions for fusion



- Implantation => T retention => VERY BAD
- Sputtering => erosion => BAD
- Sputter heavy impurities into edge plasma => cooling => GOOD
- Sputter heavy impurities into main plasma => cooling => BAD
- Sputtered molecules can migrate => redeposition => BAD
- Damage the material => worse heat conduction => BAD
- Damage the material => material becomes brittle, may crack=> BAD
- Produce gas bubbles => blisters => flaking => dust => BAD

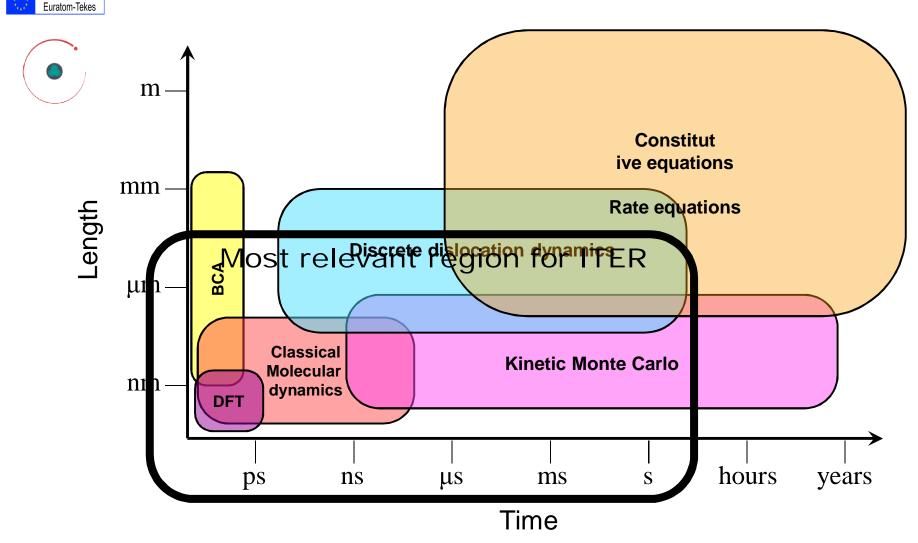
So it is very problematic from many points of view, and improved understanding is needed to understand and avoid harmful effects!



Association

Plasma-wall interactions:

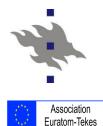
What is needed to model all this?





What is needed to model the atomic level?

- One needs to be able to handle:
- 1) keV and MeV-energy collisions between nuclei
- 2) Energy loss to electronic excitations
- 3) Transition to high-pressure and high-T thermodynamics (E $_{\rm kin} \sim$ 1 eV)
- 4) Realistic equilibrium interaction models
- 5) Phase changes, segregation, sputtering, defect production...
- 6) Long-term relaxation of defects
- Sounds daunting, but:
 - Steps 1 2 can be handled in a binary collision approximation simulation
 - Steps 1 5 can all be handled in the same molecular dynamics simulation
 - Step 6 requires kinetic Monte Carlo or rate theory



BCA = Binary collision approximation

- The original way to treat ion irradiation effects on a computer
 Developed by Mark Robinson, ~1955
 - Channeling was predicted by BCA before it was experimentally found!
- In BCA the collisions of an incoming ion are treated as a sequence of independent collisions, where the ion motion is obtained by solving the classical scattering integral
 - Based on the physics insight that at high energies, ion collision cross section with lattice atoms is low => it moves straight much of the time => most interactions can be neglected

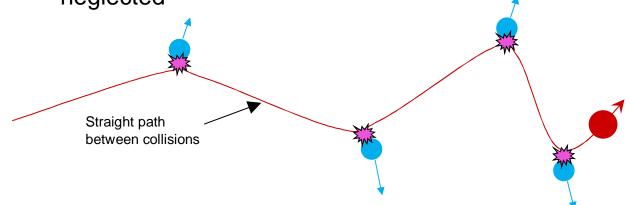
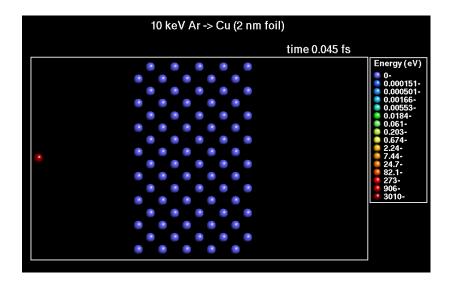




Illustration of BCA vs. MD

- 10 keV Ar -> Cu very thin foil (2 nm)
- Molecular dynamics: as realistic as possible, all atom movements taken into account
- Binary collision approximation (implemented within MD code)



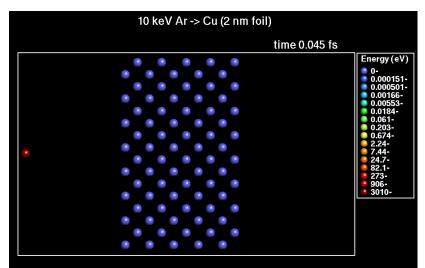


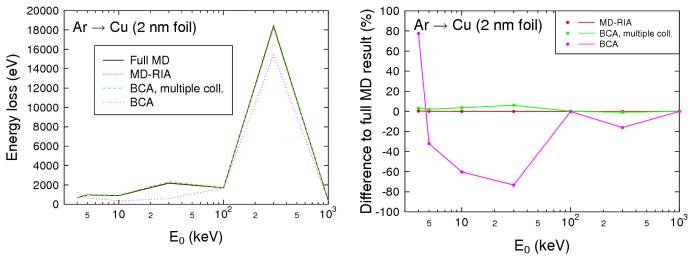


Illustration of BCA vs. MD

So was there a significant difference?

- In this particular case (5 1000 keV Ar -> Cu), yes:
 - Energy loss different even at 500 keV
 - Lower-energy recoils obviously missing from BCA
- But this was single trajectories => in an average the

difference certainly would have been much smaller!



[K. Nordlund, NIM B 266 (2008) 1886]



BCA method Illustration of BCA vs. MD

- Direct comparison by Gerhards Hobler&Betz [NIMB 180 (2001) 203] on the accuracy of MD vs. BCA in range and reflection:
 - BCA 'breakdown limit' for non-channeling implantation into
 - Si at 5 % accuracy in the projected range is

 $30M_1^{0.55}\,{\rm eV}$

where \mathbf{M}_1 is the mass of the incoming ion [NIMB 180 (2001) 203]

- E.g. Si into Si: limit is 190 eV



Different implementations

- BCA can be implemented in many different ways
 - BCA.1. "Plain" BCA : single collision at a time, static target
 - BCA.2. Multiple-collision BCA: ion can collide with many lattice atoms at the same time, static target
 - Needed at low energies
 - BCA.3. Full-cascade BCA: also all recoils are followed, static targets
 - BCA.4. "Dynamic" BCA: sample composition changes dynamically with implantation of incoming ions, ion beam mixing and sputtering
 - full-cascade mode
- Usually ran with amorphous targets ("Monte Carlo" BCA) but can also with some effort be implemented for crystals
 BCA is many many orders of magnitude more efficient than MD



BCA today and in the future?

- Historically BCA was extremely important as full MD was too slow for most practical ion irradiation purposes
- But now lots of things can be done with full MD or MD range calculations: BCA starts to get serious troubles in getting physics right below ~ 1 keV

What is the role of BCA now and in the future?

It is still ideal method for quick calculations of ion depth profiles, energy deposition, mixing, etc (BCA.1 and BCA.3)

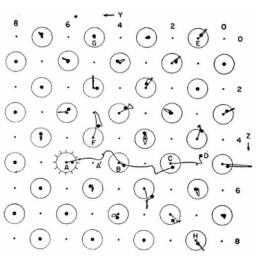
SRIM code important and very widely used

- BCA with multiple collisions (BCA.2) is largely useless now
- Dynamic BCA (BCA.4) is and will remain the best method for simulating very-high-fluence composition changes
 - As long as chemistry and diffusion does not play a role!



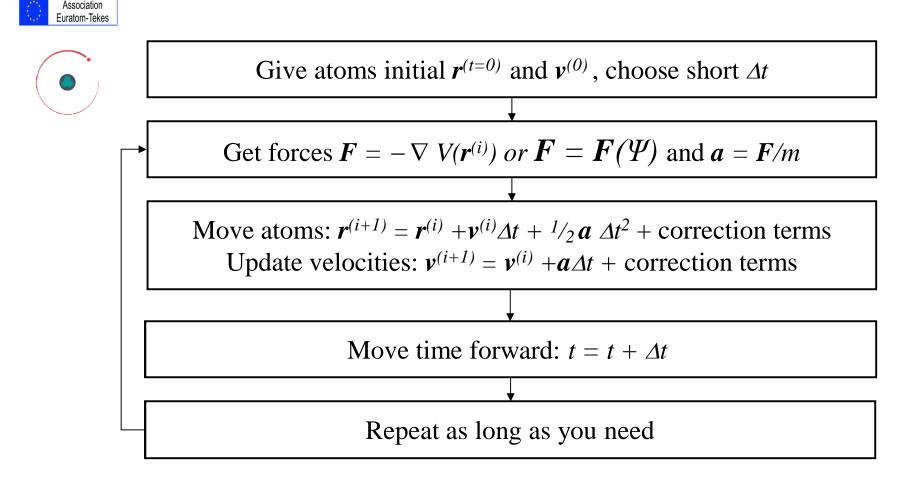
MD method in equilibrium calculations MD = Molecular dynamics

- MD is solving the Newton's (or Lagrange or Hamilton) equations of motion to find the motion of a group of atoms
 Originally developed by Alder and Wainwright in 1957 to simulate atom vibrations in molecules
 - Hence the name "molecular"
 - Name unfortunate, as much of MD done nowadays does not include molecules at all
- Already in 1960 used by Gibson to simulate radiation effects in solids [Phys. Rev. 120 (1960) 1229)]
 - A few hundred atoms, very primitive pair potentials
 - But found replacement collision sequences!





MD method in equilibrium calculations **MD algorithm**







MD – atom representations

- MD naturally needs atom coordinates (and velocities)
- Atom coordinates can simply be read in from an ASCII text file
- Simple but for atoms good enough format: .XYZ

50	00		
FCC	cell made by	makeFCC with	a= 3.52 n= 5 5 5
Cu	-7.92	-7.92	-7.92 1
Cu	-6.16	-6.16	-7.92 1
Cu	-7.92	-6.16	-6.16 1
Cu	-6.16	-7.92	-6.16 1
Cu	-7.92	-7.92	-4.4 1
Cu	-6.16	-6.16	-4.4 1
Arrays	in an MD cod	le, e.g.:	

double precision :: x(MAXATOMS),y(MAXATOMS),z(MAXATOMS)





MD – Solving equations of motion

The solution step $\mathbf{r}^{(i+1)} = \mathbf{r}^{(i)} + \mathbf{v}^{(i)}\Delta t + \frac{1}{2}\mathbf{a} \Delta t^2$ + correction terms is crucial

- What are the "correction steps"
- There is any number of them, but the most used ones are predictor-corrector type way to solve differential equations numerically:

$$\mathbf{r}^{(i+1),p} = \mathbf{r}^{(i)} + \mathbf{v}^{(i)}\Delta t + \frac{1}{2}\mathbf{a} \Delta t^2 + \text{more accurate terms}$$

Calculate
$$\mathbf{F} = -\nabla V(\mathbf{r}^{(i)})$$
 and $\mathbf{a} = \mathbf{F}/m$

Calculate corrected $r^{(i+1),c}$ based on new a



MD – Solving equations of motion

Simplest possible somewhat decent algorithm: velocity Verlet

 $\mathbf{r}(t + \Delta t) = \mathbf{r}(t) + \Delta t \mathbf{v}(t) + \frac{1}{2} \Delta t^2 \mathbf{a}(t)$ $\mathbf{v}^{\mathrm{p}} \left(t + \frac{1}{2} \Delta t \right) = \mathbf{v}(t) + \frac{1}{2} \Delta t \mathbf{a}(t)$ $\mathbf{v}^{\mathrm{c}} \left(t + \Delta t \right) = \mathbf{v}^{\mathrm{p}} \left(t + \frac{1}{2} \Delta t \right) + \frac{1}{2} \Delta t \mathbf{a}(t + \Delta t).$

[L. Verlet, Phys. Rev. 159 (1967) 98]

 Another, much more accurate: Gear5, Martyna
 I recommend Gear5, Martyna-Tuckerman or other methods more accurate than Verlet,

[C. W. Gear, Numerical initial value problems in ordinary differential equations, Prentice-Hall 1971; Martyna and Tuckerman J. Chem Phys. 102 (1995) 8071]

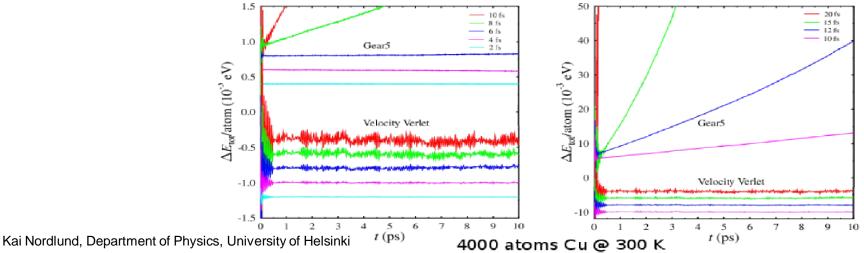
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MD – time step selection

- Time step selection is a crucial part of MD
 - Choice of algorithm for solving equations of motion and time step are related
- Way too long time step: system completely unstable, "explodes"
- Too long time step: total energy in system not conserved
- Too short time step: waste of computer time
 - Pretty good rule of thumb: the fastest-moving atom in a system should not be able to move more than 1/20 of the smallest

interatomic distance per time step – about 0.1 Å typically





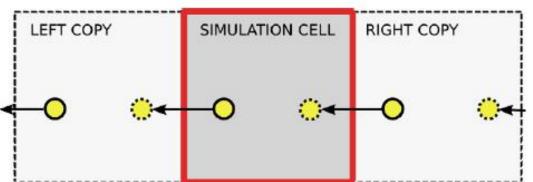
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MD – Periodic boundary conditions

- A real lattice can be extremely big
 - E.g. 1 cm^3 of Cu: 2.1e22 atoms => too much even for present-day computers
 - Hence desirable to have MD cell as segment of bigger real system

Standard solution: periodic boundary conditions

This approach involves "copying" the simulation cell to each of the periodic directions (1–3) so that our initial system "sees" another system, exactly like itself, in each direction around it. So, we've created a virtual crystal.



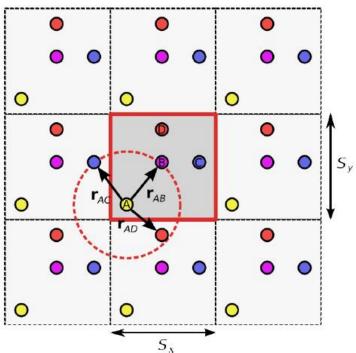


- This has to also be accounted for in calculating distances for interactions
- "Minimum image condition": select the nearest neighbour of an atom considering all possible 27 nearest cells
- Sounds tedious, but can in practice be implemented with a simple comparison:

MD: periodics continued

```
if (rijx > box(1)/2.0) rijx=rijx-box(1)
if (rijy > box(2)/2.0) rijy=rijy-box(2)
if (rijz > box(3)/2.0) rijz=rijz-box(3)

if (rijx < -box(1)/2.0) rijx=rijx+box(1)
if (rijy < -box(2)/2.0) rijy=rijy+box(2)
if (rijz < -box(3)/2.0) rijz=rijz+box(3)</pre>
```





MD – Boundary conditions



There are alternatives, though:

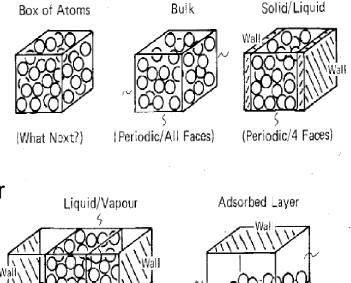
Open boundaries = no boundary condition, atoms can flee freely to vacuum

- Obviously for surfaces
- Fixed boundaries: atoms fixed at boundary
 - Unphysical, but sometimes needed for preventing a cell from moving or making sure pressure waves are not reflected over a periodic boundary
- Reflective boundaries: atoms

reflected off boundary, "wall"

Combinations of these for different

purposes



(Periodic/4 Faces)

Substrate (Periodic/4 Faces)



MD – Temperature and pressure control

- Controlling temperature and pressure is often a crucial part of MD
- "Plain MD" without any T or P control is same as simulating NVE thermodynamic ensemble
 - In irradiation simulations NVE only correct approach to deal with the collisional phase !!
- NVT ensemble simulation: temperature is controlled
 - Many algorithms exist, Nosé, Berendsen, …
 - Berendsen simple yet often good enough
- NPT ensemble simulation: both temperature and pressure is controlled
 - Many algorithms exist: Andersen, Nosé-Hoover, Berendsen
 - Berendsen simple yet often good enough



MD – cellular method and neighbour lists

- To speed up MD for large (> 100 or so) numbers of atoms, a combination of neighbour list and a cellular method to find the neighbours is usually crucial
- If one has N atoms, and want to find the neighbours for a finite-range potential, a direct search requires N² operations killing for large N
- Solution: if potential cutoff = r_{cut}, divide atoms into boxes of size >= r_{cut}, search for neighbours only among the neighbouring cells
 Neighbour list: form a list of neighbours within r_{cut}+ r_{skin} and update this only when needed

21	22	23	24	25
16	17	18	19	20
11	12	13	14	15
6	7	8	9	10
1	2	3	4	5



Nonequilibrium extensions

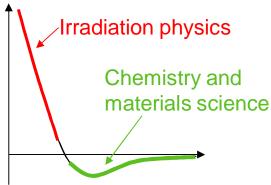
- The basic MD algorithm is not suitable for high-energy interactions, and does not describe electronic stopping at all
- But over the last ~25 years augmentations of MD to be able to handle this have been developed by us and others



What is needed to model irradiation effects?

1) keV and MeV-energy collisions between nuclei

- To handle the high-E collisions, one needs to know the high-energy repulsive part of the interatomic potential
 - We have developed DFT methods to obtain it to within
 - ~1% accuracy for all energies above 10 eV
 - So called "Universal ZBL" potential accurate to ~5% and very easy to implement
- Simulating this gives the *nuclear stopping* explicitly!



[K. Nordlund, N. Runeberg, and D. Sundholm, Nucl. Instr. Meth. Phys. Res. B 132, 45 (1997)].





1) keV and MeV-energy collisions between nuclei

- During the keV and MeV collisional phase, the atoms move with very high velocities
 - Moreover, they collide strongly occasionally
- To handle this, a normal equilibrium time step is not suitable
- On the other hand, as ion slows down, time step can increase
- Solution: adaptive time step



What is needed to model irradiation effects?

1) keV and MeV-energy collisions between nuclei

Example:

$$\Delta t_{n+1} = \min\left(\frac{\Delta x_{\max}}{v_{\max}}, \frac{\Delta E_{\max}}{F_{\max}v_{\max}}, c_{\Delta t}\Delta t_n, \Delta t_{\max}\right)$$

Here ∆x_{max} is the maximum allowed distance moved during any t (e.g. 0.1 Å), ∆ E_{max} is the maximum allowed change in energy (e.g. 300 eV), v_{max} and F_{max} are the highest speed and maximum force acting on any particle at t, respectively, c_{∆t} prevents sudden large changes (e.g. 1.1), and t_{max} is the time step for the equilibrated system.
This relatively simple algorithm has been demonstrated to be able to handle collisions with energies up to 1 GeV

[K. Nordlund, Comput. Mater. Sci. 3, 448 (1995)].

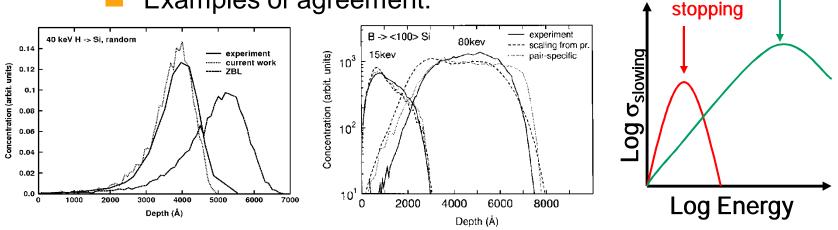




2) Energy loss to electronic excitations

- The energy loss to electronic excitations = electronic stopping can be included as a frictional force in MD
- The nice thing about this is that it can be compared directly to experiments via BCA or MD range or ion transmission calculations

Examples of agreement:



[J. Sillanpää, K. Nordlund, and J. Keinonen, Phys. Rev. B 62, 3109 (2000); J. Sillanpää J. Peltola, K. Nordlund, J. Keinonen, and M. J. Puska, Phys. Rev. B 63, 134113 (2000); J. Peltola, K. Nordlund, and J. Keinonen, Nucl. Instr. Meth. Phys. Res. B 217, 25 (2003); J. Peltola, K. Nordlund, and J. Keinonen, Nucl. Instr. Meth. Phys. Res. B 212, 118 (2003)]

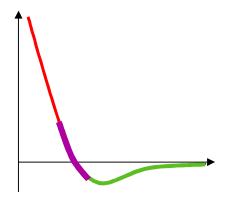
Nuclear



What is needed to model irradiation effects?

3) Transition to high-pressure and high-T thermodynamics

Requires realistic intermediate part in potential



 Can be adjusted to experimental high-pressure data and threshold displacement energies

[K. Nordlund, L. Wei, Y. Zhong, and R. S. Averback, Phys. Rev. B (Rapid Comm.) 57, 13965 (1998); K. Nordlund, J.
Wallenius, and L. Malerba. Instr. Meth. Phys. Res. B 246, 322 (2005); C. Björkas and K. Nordlund, Nucl. Instr. Meth. Phys.
Res. B 259, 853 (2007); C. Björkas, K. Nordlund, and S. Dudarev, Nucl. Instr. Meth. Phys. Res. B 267, 3204 (2008)]

Kai Nordlund, Department of Physics, University of Helsinki

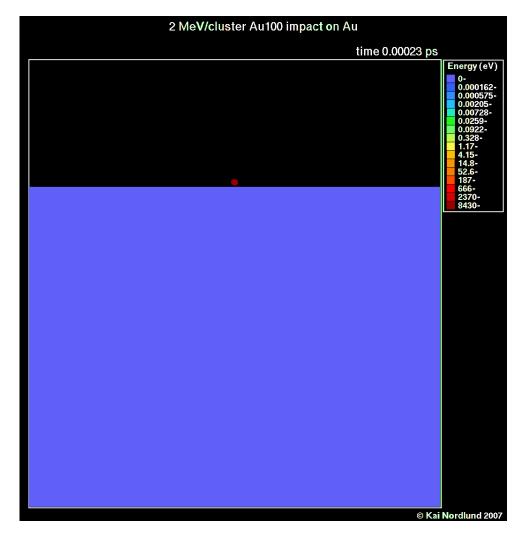


What is needed to model irradiation effects?

3) Transition to high-pressure and high-T thermodynamics

The transition to thermodynamics occurs natuarally in MD

 But boundary conditions a challenge due to heat and pressure wave emanating from a cascade



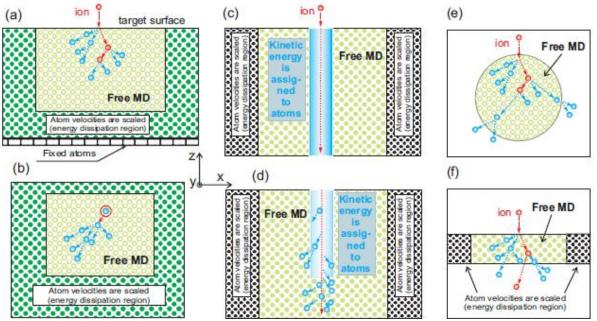


What is needed to model irradiation effects? MD irradiation temperature control

Central part has to be in NVE ensemble, but on the other hand extra energy/pressure wave introduced by the ion or recoil needs to be dissipated somehow

Exact approach to take depends on physical question:

a) surface, b) bulk recoil, c-d) swift heavy ion, e) nanocluster, f) nanowire



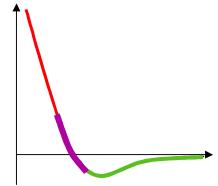
Kai Nordlund, Depa [A. V. Krasheninnikov and K. Nordlund, J. Appl. Phys. (Applied Physics Reviews) 107, 071301 (2010).



What is needed to model irradiation effects?

4) Realistic equilibrium interaction models

Finally one also needs the **normal equilibrium part** of the interaction model



- Since we start out with the extremely non-equilibrium collisional part, all chemical bonds in system can break and reform and atoms switch places
 - Conventional Molecular Mechanics force fields are no good at all!
 More on potentials later



What is needed to model irradiation effects?

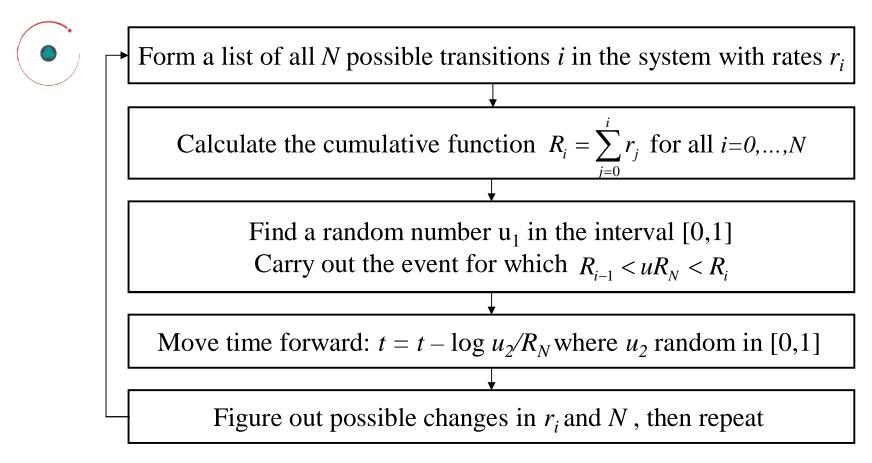
5) Long-term relaxation of defects

- The long-time-scale relaxation phase after the collisional stage can take microseconds, seconds, days or years
 - Microseconds important in semiconductors
 - Years important in nuclear fission and fusion reactor materials
- This is clearly beyond the scope of molecular dynamics
- We (and other groups in the field) have recently taken into use Kinetic Monte Carlo (KMC) to be able to handle all this
- Also rate theory (numerical solution of differential equations) can be extremely useful in this regard

[K. O. E. Henriksson, K. Nordlund, A. Krasheninnikov, and J. Keinonen, Appl. Phys. Lett. 87, 163113 (2005); K. O. E. Henriksson, K. Nordlund, A. Krasheninnikov, and J. Keinonen, Fusion Science & Technology 50, 43 (2006)]



Kinetic Monte Carlo Kinetic Monte Carlo algorithm





Kinetic Monte Carlo

Comments on KMC algorithm

- The KMC algorithm is actually exactly right for so called Poisson processes, i.e. processes occuring independent of each other at constant rates
 - Stochastic but exact
- Typical use: atom diffusion: rates are simply atom jumps
- But the big issue is how to know the input rates r_i ??
 - The algorithm itself can't do anything to predict them
 - I.e. they have to be known in advance somehow
- From experiments, DFT simulations, ...
- Also knowing reactions may be difficult
- Many varieties of KMC exist: object KMC, lattice object KMC, lattice all-atom KMC, …
 - For more info, see wikipedia page on KMC (written by me ③)



Kinetic Monte Carlo

Principles of object KMC for defects

Basic object is an impurity or intrinsic defect in lattice
 Non-defect lattice atoms are not described at all!
 Basic process is a diffusive jump, occurring at Arrhenius rate

$$r_i = r_0 e^{-E_A/k_B T}$$

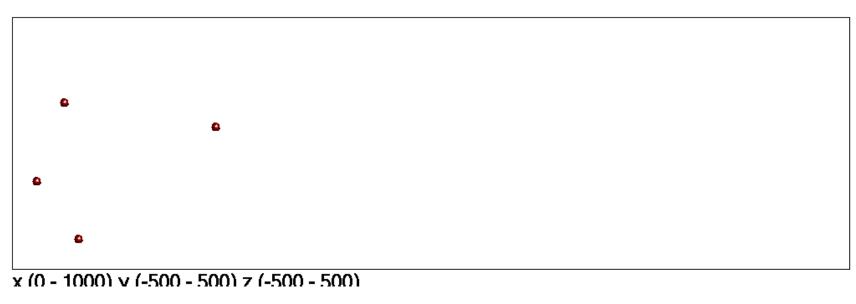
But also reactions are important: for example formation of divacancy from two monovacancies, or a pair of impurities
 Reactions typically dealt with using a simple recombination radius: if species A and B are closer than some recombination radius *r*_{AB}, they instantly combine to form defect complex



Kinetic Monte Carlo

Example animation

- Simple fusion-relevant example: He mobility and bubble formation in W
 - Inputs: experimental He migration rate, experimental flux, recombination radius of 3 Å, clusters assumed immobile



[K. O. E. Henriksson, **K. Nordlund**, A. Krasheninnikov, and J. Keinonen, Fusion Science & Technology **50**, 43 (2006).]



Interatomic potential development Equilibrium potentials

- For molecular dynamics we use **and develop** bond-order or embedded atom method type potentials
 - 3-body potentials, and sometimes more

Tersoff-like:

$$V_{i} = \sum_{\text{neighbours}} \left[V_{\text{repulsive}}(r_{ij}) + b_{ijk}(r_{ij}, r_{ik}, \theta_{ijk}) V_{\text{attractive}}(r_{ij}) \right]; b_{ijk} \propto \frac{1}{\sqrt{\text{coordination of } i}}$$

Embedded-atom method-like (EAM)

$$V_{i} = \sum_{\text{neighbours}} V_{\text{repulsive}}(r_{ij}) + F_{i}\left(\sum_{j} \rho(r_{ij})\right)$$

- Both can be motivated in the second momentum approximation of tight binding (extended Hückel approximation)
 - Related to Pauling's theory of chemical binding

[K. Albe, K. Nordlund, and R. S. Averback, Phys. Rev. B 65, 195124 (2002)]





Interatomic potential development Potential development aims

- First consider a potential for a pure element A.
- To be able to handle the effects described above, the potential should give:
 - The correct ground state: cohesive energy, crystal structure etc.
 - Describe all phases which may be relevant
 - Describe melting well
 - Describe defect energetics and structures well
- If we further consider irradiation of a compound AB:
- For high-dose irradiation the compound may segregate, so we need good models for elements A and B separately!
 - Fulfills all the requirements just given for a pure element
 - Describes well the heat of mixing of the compound
 - Describes defects involving atom types A and B well





Interatomic potential development Potential development approach

- Achieving all this starts to sound prohibitively difficult
- But there is one common factor for the main requirements:
 - Melting, defects and different phases all involve unusual atom coordination states
 - Hence if we use a framework to fit as many coordination states of the system as possible, we have some hope of getting many of the properties right

A Tersoff (Abell / Brenner)-like formalism can do this!



Interatomic potential development

Potential development approach

- We start by obtaining information on as many coordination states as possible:
 - Usually at least:

Z:	1	3	4	6	8	12
	dimer	graphite	diamond	SC	BCC	FCC
Data from experiments or DFT calculations						

Cohesive energy, lattice constant, bulk modulus for all Z
 Elastic constants for most important

Fitting done in systematic approach introduced by Prof. Karsten Albe (TU Darmstadt)



Interatomic potential development "Albe" fitting formalism

Use Tersoff potential in Brenner form (unique mathematical transformation)

$$E = \sum_{i>j} f_{ij}(r_{ij}) \left[V_R^{ij}(r_{ij}) - \underbrace{\frac{b_{ij} + b_{ji}}{2}}_{\overline{b_{ij}}} V_A^{ij}(r_{ij}) \right]$$
$$V_R(r) = \frac{D_o}{S-1} \exp\left(-\beta\sqrt{2S(r-r_o)}\right)$$
$$V_A(r) = \frac{SD_o}{S-1} \exp\left(-\beta\sqrt{2/S(r-r_o)}\right)$$

The 3 parameters r_θ, D_θ and β can be set directly from the experimental dimer interatomic distance, energy and vibration frequency!

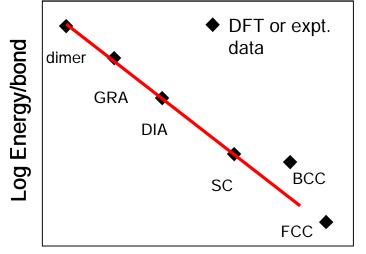


Interatomic potential development "Albe" fitting formalism

- Key idea:
 - In nn formulation,
 if material follows
 Pauling theory of
 chemical bonding,

$$E_b = -D_o \exp\left(-\beta\sqrt{2S}(r_b - r_o)\right)$$

for all coordinations



Bonding distance

[Albe, Nordlund and Averback, Phys. Rev. B 65 (2002) 195124]



Interatomic potential development "Albe" fitting formalism

- Pair-specific A-B interaction
- Three-body part modified from Tersoff form

Second-moment approximation exponential $b_{ij} = (1 + \chi_{ij})^{-1/2}$ No power of 3 $\chi_{ij} = \sum_{k(\neq i,j)} f_{ik}(r_{ik})g_{ik}(\theta_{ijk}) \exp[2\mu_{ik}(r_{ij} - r_{ik})]$ ik-dependent angular term This form for b_{ij} conforms exactly to $b_{ijk} \propto \frac{1}{\sqrt{\text{coordination of }i}}$

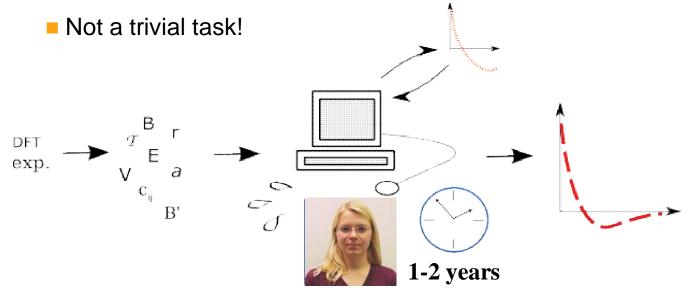
[Albe, Nordlund and Averback, Phys. Rev. B 65 (2002) 195124]



Methods:

The "blood, sweat and tears" part

- There are all in all 11 parameters that must be specified
- Constructing a good potential means finding suitable values for these
 - This is done by fitting to different experimental or densityfunctional theory values of ground state and hypothetical phases



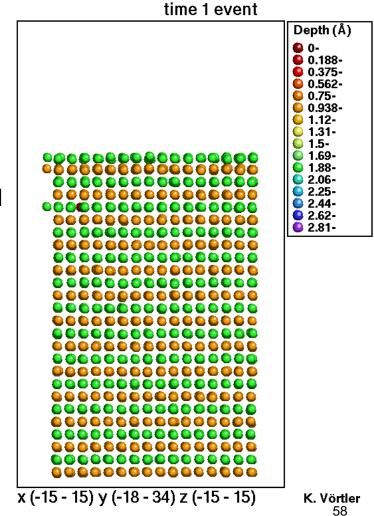


Methods:

Potentials developed

- We, and/or the Albe group, have so far developed potentials for:
 - BN, PtC, GaAs, **GaN**, SiC,
 - ZnO, FePt, BeWCH, FeCrC
 - All these potentials include all
 - the pure elements and
 - combinations!
- Fitting code "pontifix" freely availably, contact Paul Erhart
- Just to give a flavour of complexity: prolonged irradiation of WC by H and He

D + 10% He bombardment with 100 eV on C-terminated tungsten-carbide



Kai Nordlund, Department of Physics, University of Helsinki



Further reading on methods

- A full course on MD:
 - http://www.physics.helsinki.fi/courses/s/atomistiset/
- A full course on MC, including KMC:

http://beam.acclab.helsinki.fi/~knordlun/mc/2005/index.html

Books:

- Allen, Tildesley: "Computer simulation of liquids", Oxford University Press 1989
 - An old classic, still fully relevant in theory parts
- Frenkel, Smit: "Understanding molecular simulation: from algoritms to applications", Academic Press 2002
 - More modern, has e.g. Modern interatomic potentials described
- And of course all the references given in the slides

Kai Nordlund, Department of Physics, University of Helsinki



I can also for a quick introduction recommend the

Reliable (according to me) wikipedia pages

following wikipedia pages (I have written or checked and modified them myself ⁽ⁱ⁾):

- Sputtering
- Kinetic Monte Carlo
- Crystallographic defect, vacancy defect, interstitial defect, dislocation
- Collision cascade, threshold displacement energy
- Binary collision approximation

If you are not happy about any of these, do not complain to me but just fix it directly in wikipedia!



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CMS

Molecular dynamics simulation of Be, Be-C and W-C mixed divertor materials.



Carolina Björkas, Katharina Vörtler, Andrea Meinander Ane Lasa, Helga Timko, Mooses Mehine, and Kai Nordlund

Department of Physics and Helsinki Institute of Physics University of Helsinki, Finland



Contents



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- Motivation
- A few words on the methods
 - Potential development for BeCWH completed!
- Background: swift chemical sputtering of carbon
- Range of swift chemical sputtering:
 - Pure Be
 - WC (partly...)
 - BeC
 - Not in W!
- Phase formation in MD!

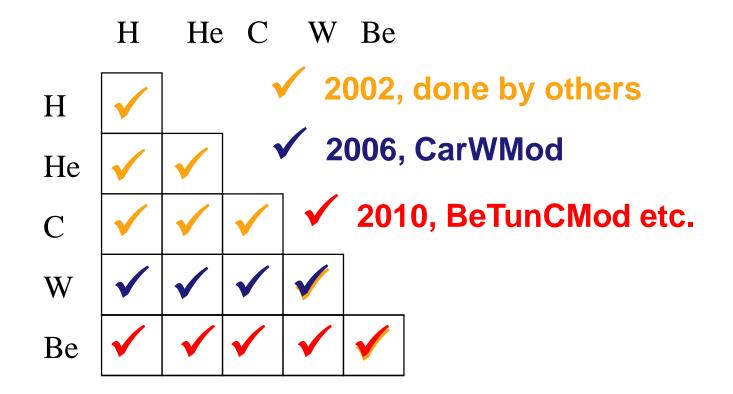
Collecting data from MD for plasma (ERO) simulations

Press-stop addition: He bubbles and migration in W



Method

Plasma-wall interaction potential availability



[WCH: Juslin et al, J. Appl. Phys. 98, 123520 (2005)]

[BeCWH: Björkas et al, J. Phys.: Condens. Matter 21 (2009) 445002; BeW: Björkas et al, J. Phys. Condens. Matter fast track 22 (2010) 352206]

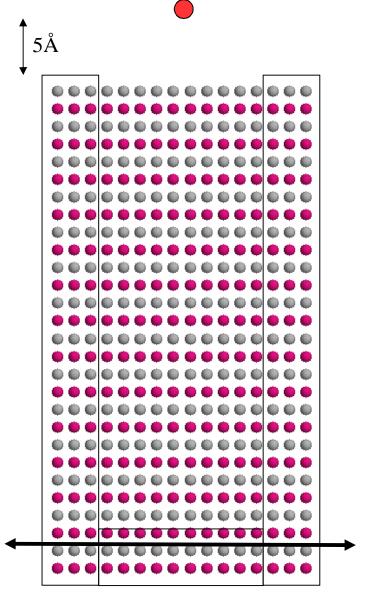


Method: plasma-wall simulation procedure



Bombarding simulations

- Bombarding distance
- Random recoil (90-100 % D, 0-10% plasma impurity)
- Temperature control on cell borders
- Bottom 2 atom layers fixed
- Simulation time: 3-5 ps



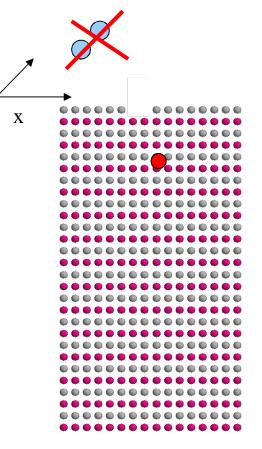


Method: Simulation procedure





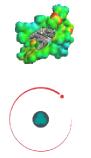
- Take out sputtered species and atoms that were implanted through the sample
- Random shift in x- and ydirection (periodic boundaries)
- Continue bombarding using this cell => cumulative simulations



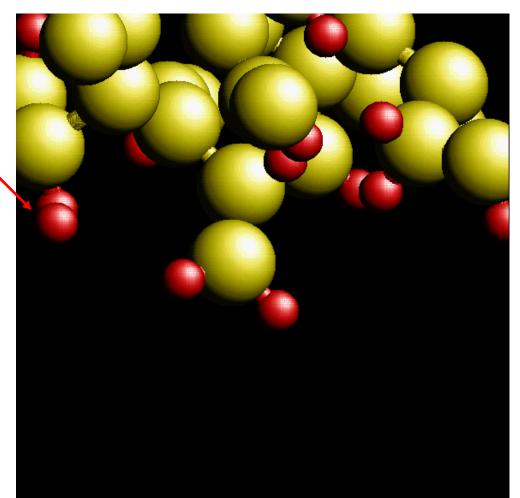




Background The swift chemical sputtering mechanism for carbon



In 1999-2000 we showed that sputtering of C can occur when incoming H happens to enter in between two carbon atoms This mechanism was not known from before



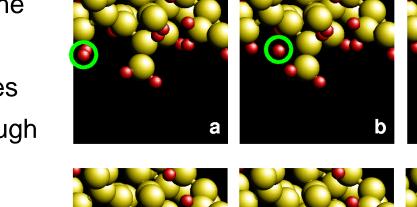


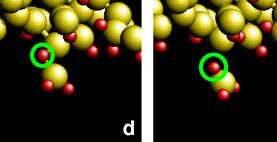
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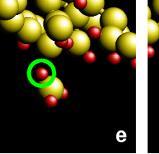
Background The swift chemical sputtering mechanism for carbon

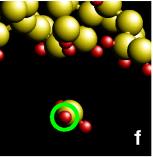
The H ion hits the middle of a C-C bond. This raises the energy enough to break the chemical bond Process is energetically unfavorable (endothermal)

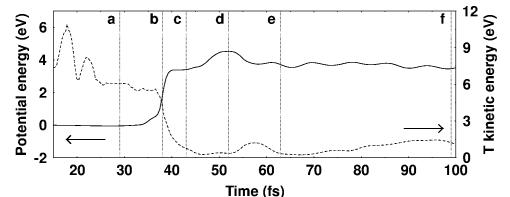
[Salonen et al, Europhys. Lett. 52 (2000) 504; Phys. Rev. B 63 (2001) 195415; Krasheninnikov et al, Comput. Mater. Sci. 25 (2004) 427]













Swift chemical sputtering of carbon:

The carbon sputtering mechanism



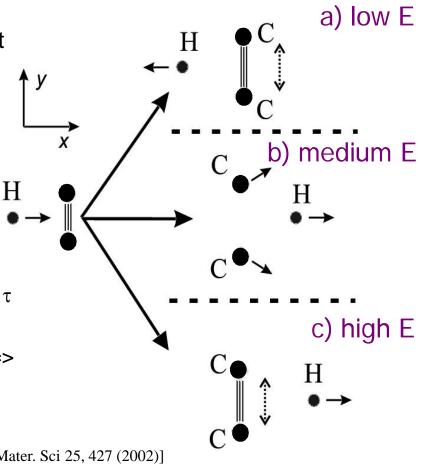
Physical insight

A model system of a single H atom colliding with a C dimer gives insight to the basic mechanism

Momentum transfer in y direction is

$$p_y = \int_{-\infty}^{\infty} f_y(t, E_{kin}[\mathbf{H}]) dt \approx \bar{f}_y \bar{\tau}$$

- a) low E: H does not penetrate and is reflected
- b) medium E: H penetrates slowly => large τ
 => large p_y => bond breaking occurs
- c) high E: H penetrates rapidly => small τ => small p_{v} => no bond breaking





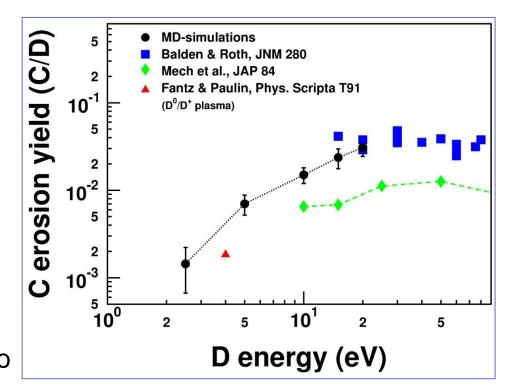
Background

Comparison with experiments

The sputtering we observed is in decent agreement with experiments!

Even better
 agreement
 demonstrated later
 by P. Krstic
 At higher E and T also

other mechanisms certainly are active



[Salonen, Physica Scripta T111 (2004) 133; Krasheninnikov et al, Comput. Mater. Sci. 25 (2004) 427; Nordlund et al, Pure and Appl. Chem. 78 (2005) 1203]



Contents - update



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Motivation

A few words on the methods

Scientific background: swift chemical sputtering of carbon

Range of swift chemical sputtering:

- Pure Be
- WC
- BeC
- Not in W!
- Phase formation in MD!

Collecting data from MD for plasma (ERO) simulations

Press-stop addition: He bubbles and migration in W



Swift chemical sputtering of beryllium: **Background**





Can metals erode chemically??

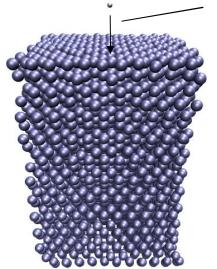
Conventional wisdom says no, but the recent experiments by Doerner showed that ~50 eV D bombardment of Be erodes most Be in BeD molecules => cannot be physical sputtering

We bombarded beryllium surfaces with D ions up to 100

eV

Distance 5 Å

Cell of 3400 atoms





Swift chemical sputtering of beryllium:

Interlude: Check of model for Be self-sputtering





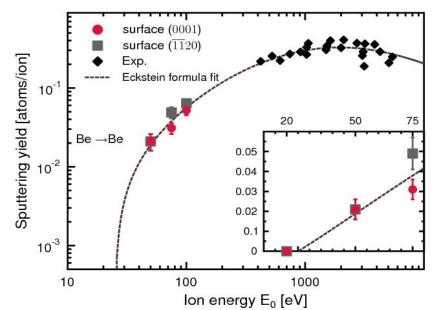
20 – 100 eV Be ion

irradiation

- flux ~2.10²⁵ m⁻²s⁻¹
- @ room temperature
- Threshold 20 50 eV
- Yield agrees with exp.
 - Exp. values only at keV

energies

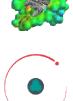
- Be does not amorphize
 - Like a typical metal





Swift chemical sputtering of beryllium:

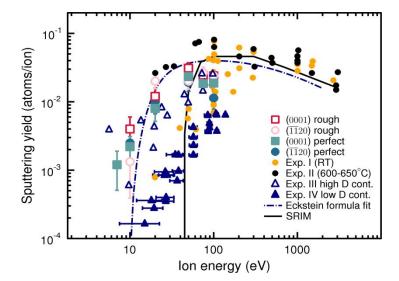
D irradiation of pure Be



Our simulations agree with plasma experiments done at the PISCES-B facility at low energies

> At higher energies with the rest

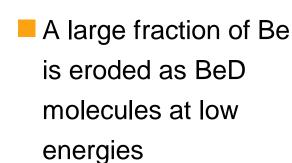
Sputtering is seen at 7 eV!



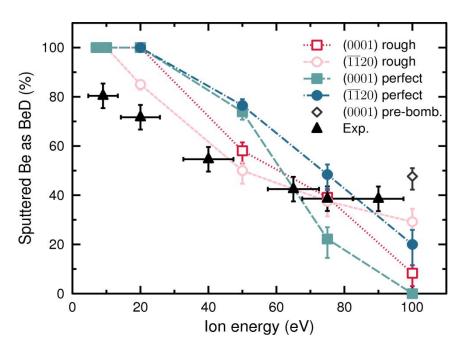


Swift chemical sputtering of beryllium: **D irradiation of pure Be**





 Chemical sputtering!
 This fraction decreases with ion energy
 The same trend is seen in the experiments by Doerner



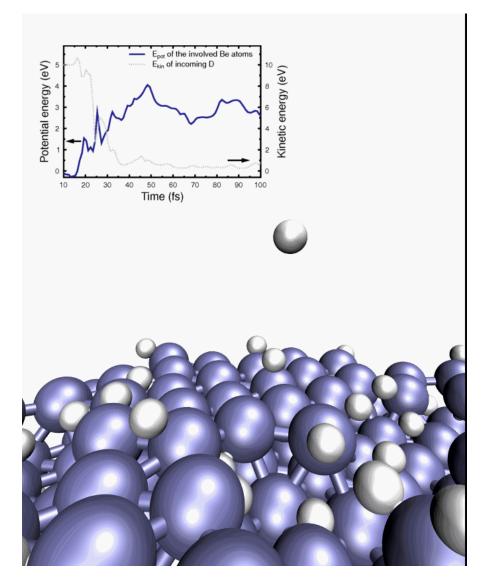


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Swift chemical sputtering of beryllium:

D irradiation of Be





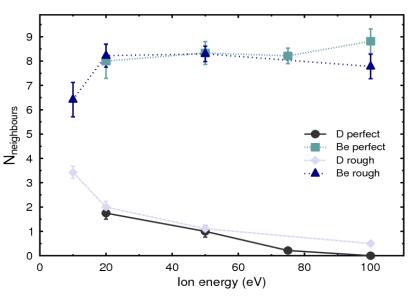
Swift chemical sputtering of beryllium: D irradiation of Be





The movie shows a swift chemical sputtering process

- Low-energetic D ions release Be atoms from the surface by breaking Be-Be bonds
- This is possible since a surface Be atom that has bonds with D, has a weakened binding to the surface
 - At low energies, Be atoms are likely to have D neighbours
 - The figure shows
 the initial neighbours
 of the sputtered
 Be atoms





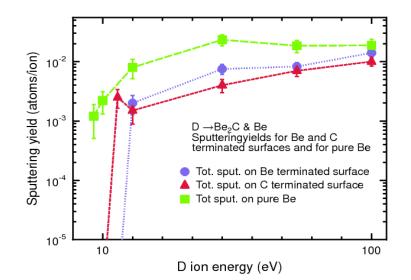
Swift chemical sputtering of BeC D irradiation on Be₂C

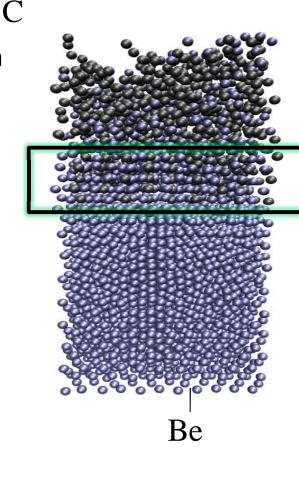




Carbide layers will form on beryllium surfaces

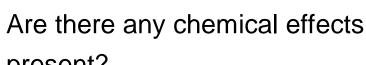
This is believed to decrease the sputtering of pure Be and pure C
 Noticeable in our simulations



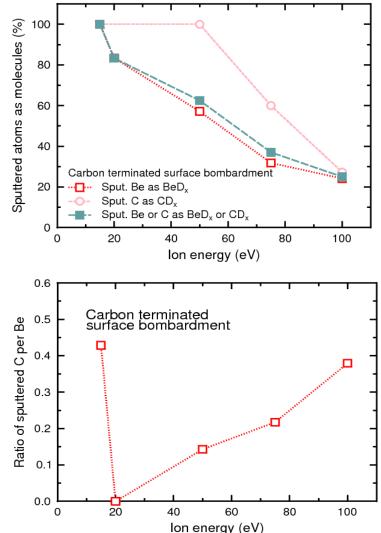




Swift chemical sputtering of BeC **D irradiation on Be₂C**



- present?
- Yes, molecules are sputtered!
 - Same mechanism as in pure Be: the swift chemical sputtering mechanism
- Preferential sputtering of Be
 - 15 eV case interesting
 - Here, but not at 20 eV, one
 - CD_3 and one CD_4 are released
 - Statistical fluctuations





Swift chemical sputtering of BeC Irradiation of Be₂C



Molecules sputtered: mostly BeD

	D energy	Be	BeD	BeD ₂	BeD ₃	BeC	С	C ₂	CD	CD3	CD4	Tot sput.	No.bomb.
	10eV	0	0	0	0	0	0	0	0	0	0	0	3200
	15eV	0	0	0	0	0	0	0	0	0	0	0	4000
Desurf	20eV	0	4	2	1	0	0	0	0	1	0	8	4000
Be-surf.	50eV	11	14	3	0	1*	0	0	0	0	0	30	4000
	75eV	15	15	3	0	0	0	0	0	0	0	33	4000
	100eV	34	16	3	0	0	1	0	0	0	0	54	4000
	10eV	0	0	0	0	0	0	0	0	0	0	0	2400
C-surf.	15eV	0	4	2	0	1^{**}	0	0	0	1	1	10	4000
	20eV	1	4	1	0	0	0	0	0	0	0	6	4000
	50eV	6	7	1	0	0	0	0	0	2	0	16	4000
	75eV	15	6	2	0	0	2	1	1	0	0	27	4000
*1.6.4.70	100eV	22	6	0	0	1	0	8	1	1	0	40	4000

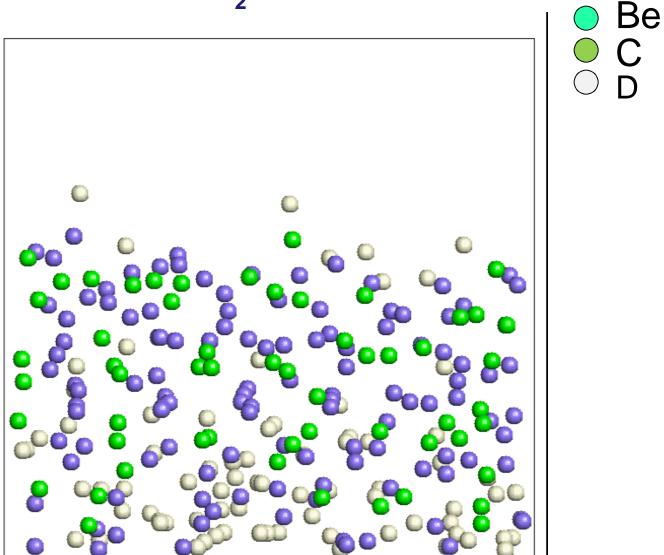
*In fact, 7 BeDCD molecule was sputtered

**In fact, a BeDCD₃ nolecule was sputtered



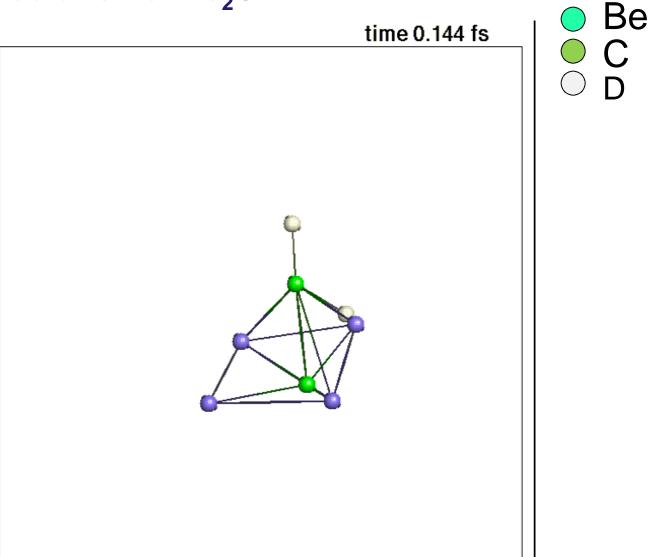








Swift chemical sputtering of BeC Irradiation of Be₂C









Swift chemical sputtering of BeC **D irradiation of WC**



Molecular sputtering was also observed in WC sputtering simulations (e.g. at 300 eV):

100% D	3953	67 C,	2 CD, 4 C ₂
90% D 10% C	2000	175 C	2 CD, 1 C ₂ , 8 CW, 1 CWD, 2 W
90% D 10% W	5000	146 C	4 C2, 30 CW, 1 C2W, 1 CWD, 68 W, 3 WD
90% D 10% He	2000	30 C	
90% D 10% Ne	2000	92 C,	$1 \text{ CD}, 4 \text{ C}_2, 9 \text{ CW}, 1 \text{ C}_2 \text{W}, 1 \text{ W}_2 \text{C}, 2 \text{ W}$
90% D 10% Ar	5000	215 C	$3 \text{ CD}, 1 \text{ C}_2\text{D}, 8 \text{ C}_2, 43 \text{ CW}, 1 \text{ C}_2\text{W}, 4 \text{ WCD}, 1 \text{ WC}_2\text{D}, 2 \text{ CW}_2, 65 \text{ W}, 4 \text{ WD}$
100% Ar	5000	631 C	$10 C_2, 1 C_3, 173 CW, 11 C_2W, 10 CW_2, 1 C_3W, 387 W, 12 W_2$

A lot of different small molecules

Very few hydrocarbons, WC-molecules and single C preferred

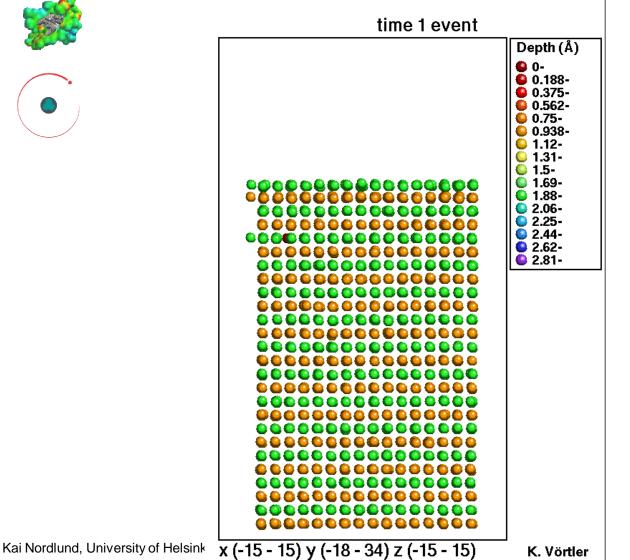
Is the mechanism the same as in Be and Be₂C?

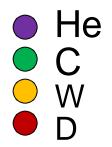


Sputtering of WC

D irradiation of WC

D + 10% He bombardment with 100 eV on C-terminated tungsten-carbide





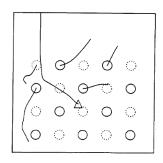


Sputtering of WC D irradiation of WC





- Detailed analysis showed that the mechanism is essentially the dimer physical sputtering one
 - Synergetic movement of atoms in low-energy heat spikes
 - Physical in nature, mostly seen during Ar sputtering
 - So, not the same as during the low energy bombardments of beryllium and beryllium carbide



Karetta and Urbassek Appl. Phys. A 55 (1992) 364

At lower energies, however, mechanism will again be swift chemical sputtering





D + impurity irradiation of WC





The impurities (10% W, C, He, Ne or Ar) resulted in

- 10% W: Net deposition of W
- 10% C: Net deposition of C
- 10% He: A few molecules sputtered
- 10% Ne: Molecules sputtered
- 10% Ar: Many molecules sputtered

Increasing amount of sputtered molecules

An enhancement of the sputtering yield of W was observed, so that e.g.

$$Y_{90\%D+10\%Ar} > 0.9Y_{100\%D} + 0.1Y_{100\%Ar}$$







Sputtering of W D irradiation of pure W

- As a sanity check for our potentials, we also ran simulations of D bombardment of pure W
- Experiments show zero sputtering below ~ 200 eV, so we should also get none – otherwise we are in trouble with our swift chemical sputtering results!
- Fortunately we do get zero sputtering, for at least 2000 D ions up to 100 eV
 - Higher energies running still, eventually physical sputtering must appear

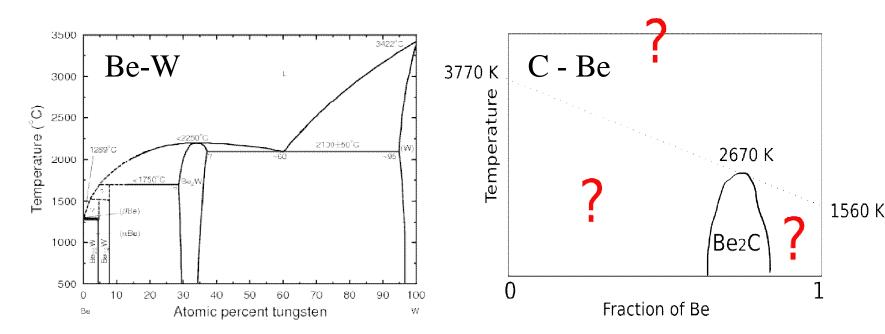






Phase formation in MD Observations of phase formation

- Our interatomic potentials aim to describe all crucial phases of the materials involved correctly.
- Hence they should be able to reproduce the central part of the phase diagrams – to the extent they are known...





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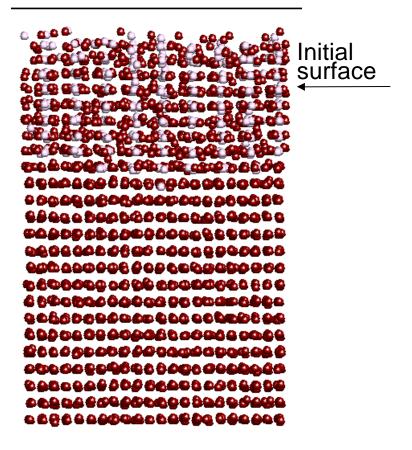
Phase formation in MD C irradiation of Be

Gratifyingly enough, we do see a lot of phases formed!

20 – 100 eV C ion irradiation

- flux ~2·10²⁵ m⁻²s⁻¹
- **=** @ 1500 K

Layers of Be₂C are formed! C (100 eV) -> (0001) Be



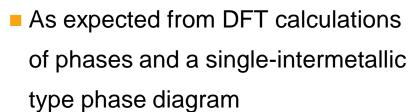


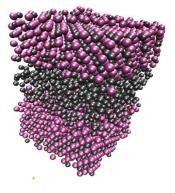




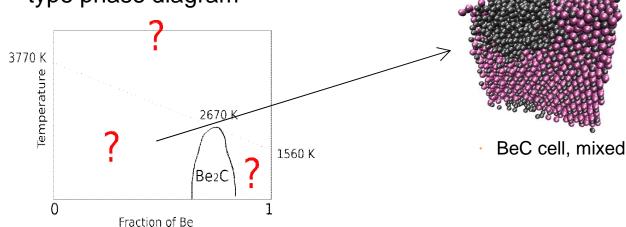
Phase formation in MD Random mixtures of Be and C

When making cells of random Be-C composition, we do see phase separation of BeC starting from random mixtures!





layered BeC





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Simulations of H and He effects in W



CMS

Kalle Heinola,

Krister Henriksson,

Tommy Ahlgren, Katharina Vörtler and Kai Nordlund

Department of Physics University of Helsinki, Finland





Bubble formation and blistering in W:

Motivation

- The main divertor material in ITER will be W
- So what about H and He damage in it?
- One of the main advantages of W is that 1-100 eV H and He cause zero damage, very little physical sputtering and no chemical sputtering
- But these ions do produce bubbles and blisters, which eventually rupture and might cause erosion







Bubble formation and blistering in W:

Difference of H and He bubble formation

Depth of blisters vastly different.

- H: at micrometer depths
- He: close to projected range (<100 Å)</p>
- Why is this?

We considered many possibilities:

- Damage different: no, since also non-damaging irr. produces bubbles!!
- Difference in diffusivity: no, about the same
- Thermal gradients: no
- Different kinds of W samples in experiments: no

But how about differences in trapping behaviour?

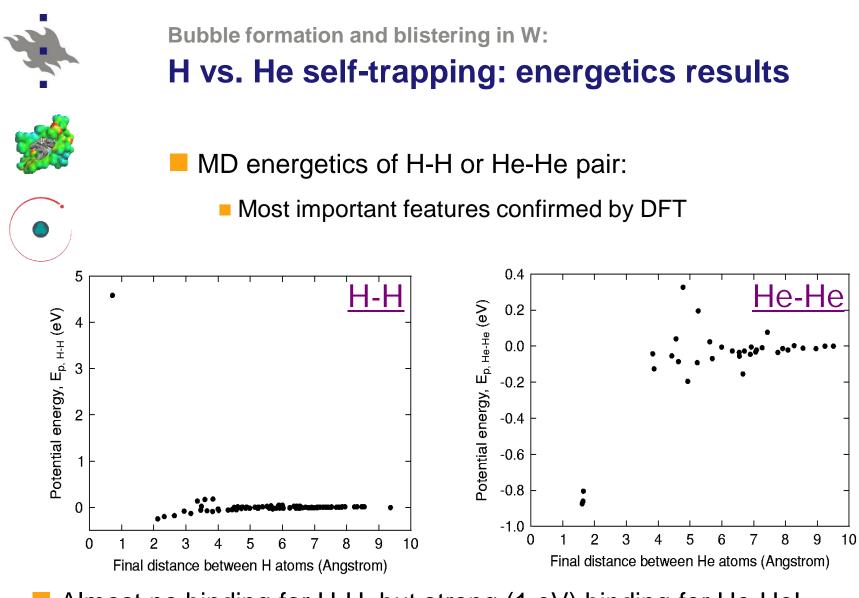






Bubble formation and blistering in W: H vs. He self-trapping

- The simplest possible trap is the self-trap: two mobile atoms A and A clustering with each other
 - Becomes immobile, acts as seed for further bubble growth
- To examine this, we used classical MD simulations and quantum-mechanical DFT calculations to examine the energy of two H or He atoms at different distances



Almost no binding for H-H, but strong (1 eV) binding for He-He!

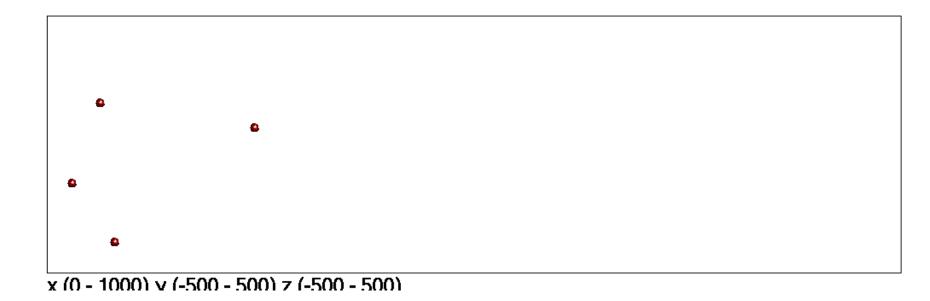
[K. O. E. Henriksson, K. Nordlund, A. Krasheninnikov, and J. Keinonen, Appl. Phys. Lett. 87, 163113 (2005)] Kai Nordlund, University of Helsinki

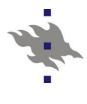


Bubble formation and blistering in W: Animation of KMC bubble formation



He bubble formation: mobile atoms red, immobile He in clusters orange, large clusters green or blue





Bubble formation and blistering in W: He bubble depths

- This shows that He can self-trap, while H can not
- Enough to explain qualitatively He-H difference
 - But to be on the safe side we also used Kinetic Monte Carlo (KMC) simulations of He migration in W to check whether He bubble depths obtained with self-trapping are the same as in experiments
- Results:

<u>T(K)</u>	<u>Our KMC</u>	<u>Expt.</u>	<u>Reference</u>
300	100 Å	62 Å	Nicholson and Walls 1978
2370	2200 Å	0 – 5000 Å	Chernikov and Zakharov 1989

[K. O. E. Henriksson, K. Nordlund, A. Krasheninnikov, and J. Keinonen, Appl. Phys. Lett. 87, 163113 (2005); K. O. E. Henriksson, K. Nordlund, A. Krasheninnikov, and J. Keinonen, Fusion Science & Technology 50, 43 (2006)]
Kai Nordlund, University of Helsinki

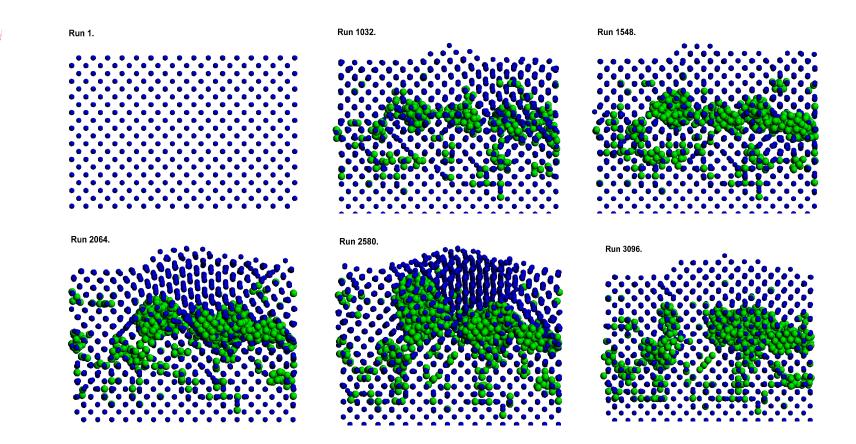


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Bubble formation and blistering in W:

Near-surface blistering of W by He

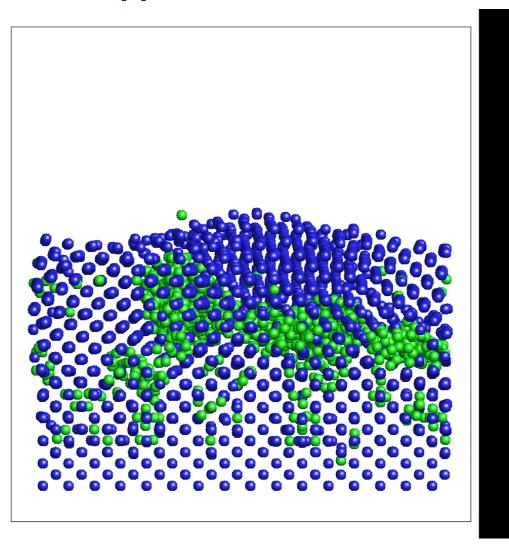
MD simulation of 100 eV He -> W:





0

Bubble formation and blistering in W: What happened after run 2580?



[K. O. E. Henriksson, K. Nordlund, and J. Keinonen, Nucl. Instr. Meth. Phys. Res. B. 244, 377 (2005)] Kai Nordlund, University of Helsinki



Bubble formation and blistering in W: **Blistering results**



In the He-induced blistering events observed so far, no W erosion associated with the bubble rupture has occurred

Sounds encouraging: low-E bombardment bubble rupture may not cause much erosion

The results look very much like the first stages of the formation of Doerner's W fuzz!







Bubble formation and blistering in W:

Recent results: traps for T in W divertors

- Neutrons induce damage also in the W divertor
- This damage may bind T coming from the fusion plasma
- Retained T limits the usage lifetime of ITER (700 g limit)
 - Hence it is important to know the nature of the damage in W, how much T it can retain, and how it can be taken out
- To this end, we are doing multiscale modelling of the damage and T binding in W



Multiscale calculation of H retention with Rate Equations:

Association Euratom– Tekes Hydrogen in the bulk is free (=mobile) or trapped

E.g. system with hydrogen and monovacancies (V₁), C = C(x, t)

$$\frac{\partial C_a}{\partial t} = D_a \frac{\partial^2 C_a}{\partial x^2}$$

diffusion

(free particles $D = D_0 e^{-E_m/kT}$)



- several defect types trap Hydrogen
- evolution of defects is time & temperature dependent

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Multiscale calculation of H retention with Rate Equations:

Association Euratom–Tekes Analytical method, real time & length scales, no limitations in the number of particles

$$\frac{\partial C_{\alpha}(x,t)}{\partial t} = D_{\alpha} \frac{\partial^2 C_{\alpha}(x,t)}{\partial x^2} + S_{\alpha}(x,t) \pm \sum_{\beta,\gamma=1}^{N} k_{\beta,\gamma}^2 D_{\beta} C_{\beta}(x,t) \pm \sum_{\delta=1}^{N} \nu_{\delta} e^{-E_{A,\delta}/kT} C_{\delta}(x,t)$$

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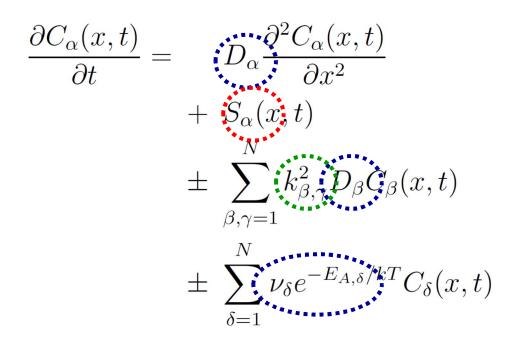
H	+ $\mathbf{V}_m \mathbf{H}_n$	$-1 \iff \mathbf{V}_m \mathbf{H}_n$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$
Н	+ $\mathbf{I}_m \mathbf{H}_n$	$\mathbf{I}_{m}\mathbf{H}_{n}$	$1 \le m \le 10 \\ 0 \le n \le m \qquad \bullet \rightarrow \bullet \bullet$
\mathbf{I}_m	+ $\mathbf{I}_i \mathbf{H}_j$	\Rightarrow I _{m+i} H _j	$m+i \leq 10$ $\longrightarrow \longleftarrow \bigoplus \implies \bigoplus$
\mathbf{I}_m	+ $\mathbf{V}_i \mathbf{H}_j$	$ = \begin{cases} m+i & j \\ j & \mathbf{H} \\ \mathbf{V}_{i-m} & \mathbf{H}_{j} \\ \mathbf{I}_{m-i} & \mathbf{H}_{j} \end{cases} $	$ \begin{array}{c} m = i \\ m < i \\ m > i \end{array} \left\{ \begin{array}{c} \bullet \rightarrow \\ \bullet \rightarrow \\ \bullet \end{array} \right\} \left\{ \begin{array}{c} \bullet \rightarrow \\ \bullet \rightarrow \\ \bullet \end{array} \right\} \left\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \\ \bullet \end{array} \right\} \left\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \\ \bullet \rightarrow \end{array} \right\} \left\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \\ \bullet \rightarrow \end{array} \right\} \left\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \rightarrow \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \bullet \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \bullet \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \bullet \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \bullet \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \bullet \bullet \end{array} \right\} \left\{ \begin{array}{c} \bullet \bullet \\ \\ \bullet \end{array} \right\} \left\{ \begin{array}{c} \bullet \\ \bullet \end{array} \right\} \left\{ \begin{array}{c} \bullet \\ \bullet \end{array} \right\} \left\{ \begin{array}{c} \bullet \\ \bullet \\ \\ \left\{ \begin{array}{c} \bullet \bullet \end{array} \right\} \left\{ \begin{array}{c} \bullet \\ \\ \bullet \end{array} \right\} \left\{ \begin{array}{c} \bullet \\ \\ \bullet \end{array} \right\} \left\{ \begin{array}{c} \bullet \\ \\ \\ \left\{ \end{array}\right\} \left\{ \begin{array}{c} \bullet \end{array} \right\} \left\{ \begin{array}{c} \bullet \\ \\ \\ \\ \left\{ \end{array}\right\} \left\{ \begin{array}{c} \bullet \end{array} \right\} \left\{ \left\{ \begin{array}{c} \bullet \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ $
V	+ $\mathbf{V}_m \mathbf{H}_{j}$	$n \Rightarrow \mathbf{V}_{m+1}\mathbf{H}_n$	$\begin{array}{c} 1 \leq m \leq 4 \\ 0 \leq n \leq 6 m \end{array} \longrightarrow \begin{array}{c} \bullet \bullet$
H	+ G, ρ	←→ G,ρ(H)	Trapping in grains/disloc. $\bullet \rightarrow$ \checkmark \iff \checkmark
H	+ Imp	a ↔ Imp _a (H	
Н	+ S	↔ S, H	Surface $\bullet \rightarrow \bullet \Leftrightarrow \bullet$
Ever	nts not inc	luding hydroge	en
V	+ V_m	\iff V _{m+1}	$1 \le m \le 4$ $\bigcirc \rightarrow \leftarrow \bigcirc $
\mathbf{V}_m	+ V_n	\Rightarrow V _{<i>m</i>+<i>n</i>}	$m+n \leq 5$ \longrightarrow \longleftarrow \longrightarrow \longrightarrow \longrightarrow \longrightarrow \longrightarrow \longrightarrow
Ι	+ I _m	\iff I _{m+1}	$1 \le m \le 9$ $\longrightarrow \longleftarrow \bigcirc $
I _m	+ I _n	\implies I _{m+n}	$m+n \le 10$ $\longrightarrow \longleftarrow \bigcirc $
I _m	+ V_n	$\Rightarrow \begin{cases} \emptyset \\ \mathbf{V}_{n-m} \\ \mathbf{I}_{m-n} \end{cases}$	m = n $m < n$ $m > n$ $m > n$
V	+ G ,ρ	→ G ,ρ	Grain or dis- location sink \rightarrow \rightarrow \rightarrow
V	+ Imp	a ↔ Imp _a (V	$\begin{array}{ccc} & \text{Impurity} \\ a = 1, 2 \end{array} \qquad \qquad$
V	+ S	⇒ S	Surface \rightarrow \rightarrow
\mathbf{I}_m	+ G ,ρ	⇒ G,ρ	Grain or dislocation sink \longrightarrow \rightarrow \rightarrow
Ι	+ Imp	a ↔ Imp _a (I)	$\begin{array}{c} \text{Impurity} \\ a=1,2 \end{array} \bullet \bullet \bullet \bullet \bullet \bullet \bullet \bullet \bullet $
I _m	+ S	⇒ S	Surface \rightarrow \rightarrow \rightarrow $)2$



Euratom-Tekes

Multiscale calculation of H retention with Rate Equations:

- Analytical method, real time & length scales, no limitations in the number of particles
- System with hydrogen, vacancies (V_n) , interstitials (I_n) , grains, ...









sink strength and reaction radii from MD



source term from BCA, MD, experiments,

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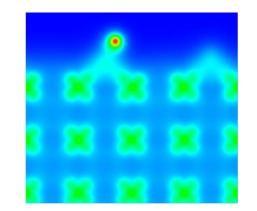
etc



Multiscale calculation of hydrogen retention in W: Computational tools

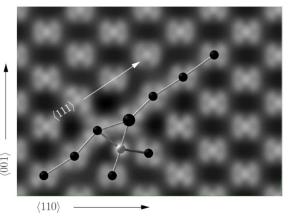
	Association Euratom–Tekes
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- Energetics from first-principle calculations
 - DFT (density functional theory) with VASP 4.6.35
 - W properties: bulk bcc, fcc and A15 as well as W₂ molecule
 - W point defect properties (mono-vacancy and SIA)
 - W (100) surface reconstruction
 - H diffusivity in W and on the (100) surface
 - H detrapping from W mono-vacancy



H @ W(100) surface

H @ (111) SIA



Ahlgren, Heinola, et al, J. Appl. Phys. **107**, 033516 (2010) Heinola, Ahlgren, J. Appl. Phys. **107**, 113531 (2010) Heinola, Ahlgren, Phys. Rev. **B 81**, 073409 (2010) Heinola, Ahlgren, et al, Phys. Rev. **B 82**, 094102 (2010)

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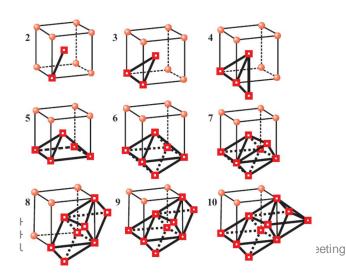
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Multiscale calculation of hydrogen retention in W: Computational tools



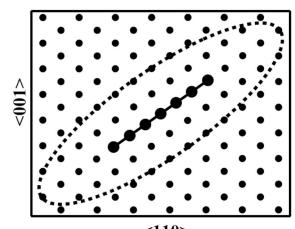
- Energetics from first-principle calculations
 - DFT (density functional theory) with VASP 4.6.35
- Defect properties in clusters with MD
 - MD potential from DFT + experiments
 - clustering & annihilation radii (R)
 - W in W projected ranges with low energies
 - thousands of W atoms



← Vacancy cluster properties

Frenkel pair

annihilation radius ightarrow



<110>

Ahlgren, Heinola, et al, J. Appl. Phys. 107, 033516 (2010)



Multiscale calculation of hydrogen retention in W: Computational tools

Association Euratom– Tekes

- Energetics from first-principle calculations
 - DFT (density functional theory) with VASP 4.6.35

Defect properties in clusters with MD
 MD potential from DFT + experiments

Initial damage profile with **MD** & **BCA** (binary collision approx.):

- damage profile vs. depth per implanted ion
- immediate SIA & vacancy clustering: I₁₋₅, V₁₋₁₀



Multiscale calculation of hydrogen retention in W: Computational tools

Association Euratom– Tekes

- Energetics from first-principle calculations
 - DFT (density functional theory) with VASP 4.6.35

Defect properties in clusters with MD
 MD potential from DFT + experiments

Initial damage profile with MD & BCA (binary collision approx.):
 damage profile vs. depth per implanted ion

Final damage profile with **Rate Equations** $t_{i+1} = t_i + \Delta t$

- diffusion
- trapping, detrapping
- clustering
- e.g. D implantation 30 mins @ RT, annealing for 24 hrs

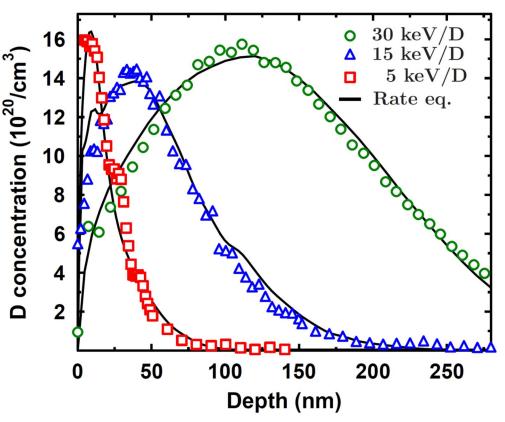
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Association Euratom– Tekes Validation of the *Multiscale* method: Rate Equations vs. Implantation experiments

Rate Equation results:

- Same input parameters as in the experiments: 5, 15, 30 keV/D and 5.8×10¹⁶ D/cm²
- D implantation 30 mins @ RT, annealing 24 hrs
- Excellent agreement with the experiments



Experimental:

Ahlgren, Heinola, et al., Nucl. Instr. Meth. B, **249**, (2006) Heinola, Ahlgren, et al., Phys. Scripta, **T128** (2007)

Theory:

Ahlgren, Heinola, et al. Phys. Rev. B (2010), submitted⁸

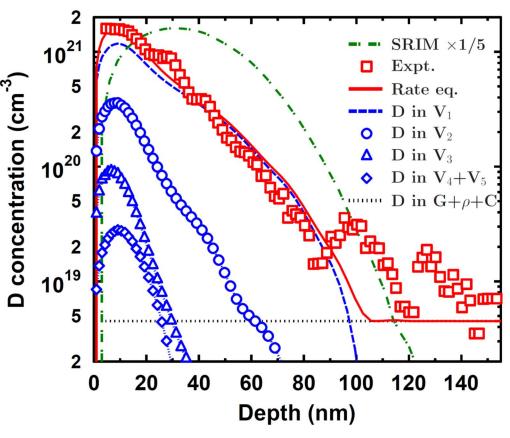


Association Euratom– Tekes Validation of the *Multiscale* method: Rate Equations vs. Implantation experiments

5 keV D in W

Rate Equation results:

- Specification of each defect type
- Hydrogen trapping to each defect
- Majority of hydrogen in mono-vacancies (V₁) with all implantation energies
- High implantation energy
 - → number of larger defects increase



- G+ρ is the **only** adjustable parameter
- $(G+\rho \text{ is dislocation and grain boundary sinks})$
- C is the inherent C impurity concentration [Plansee]

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Ahlgren, Heinola, et al., Phys. Rev. B (2010), submitted

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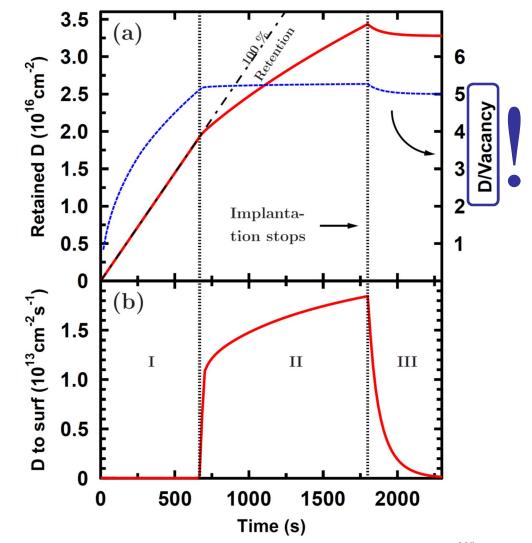


Multiscale method: Rate Equations



Retention & recycling

- Accumulation of D to the W surface in the course of implantation
 - \rightarrow Hydrogen recycling



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Ahlgren, Heinola, et al., Phys. Rev. B (2010), submitted ¹¹⁰







Conclusions - W

- Bubble formation and trapping in W by H and He is dramatically different
- Experiments on D trapping can be reproduced by a multiscale modelling scheme
 - Combining results from DFT+MD+BCA/MD with an analytical set of Rate Equations for realistic length and time scales
 - Implantation and diffusion of D in W (@ RT) and grain boundaries and impurities included in the system
 - Model and experiments on 5, 15 and 30 keV/D implantations and with 5.8x10¹⁶ D/cm² were shown to be in excellent agreement